

VTR-H Diode 1N4001 THRU 1N4007

GENERAL PURPOSE SILICON RECTIFIER

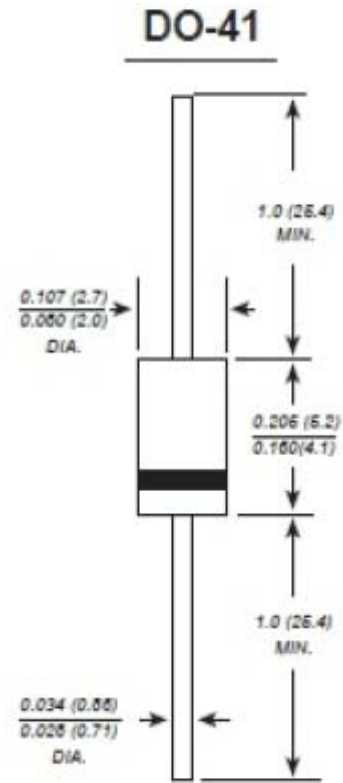
Reverse Voltage 50 to 1000V * Forward Current 1.0A

Features:

- The plastic package carries Underwriters Laboratory Flammability Classification 94V-0
- Construction utilizes void-free molded plastic technique
- Low Reverse Leakage
- High forward surge current capability
- High temperature soldering guaranteed: 250 /10 seconds
- 0.375"(9.5mm)lead length,5lbs.(2.3kg) tension.

Mechanical Data:

Case : JEDEC DO-41 molded plastic body
 Terminals: Plated axial leads, solderable per MIL-STD-750 Method 2026
 Polarity : Color band denotes cathode end
 Mounting Position : Any
 Weight : 0.012 ounce, 0.33 grams



Dimensions in inches and (millimeters)

Maximum Rating and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified

Single phase half-wave 60HZ resistive or inductive load ,for capacitive load current derate by 20%

Items	Symbols	1N 4001	1N 4002	1N 4003	1N 4004	1N 4005	1N 4006	1N 4007	UNITS
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum Average Forward Rectified Current 0.375"(9.5mm) lead length at TA=75°C	$I_{(AV)}$	1.0							AMP
Peak forward surge current 8.3ms single Half sine-wave superimposed on rated toad (JEDEC Method)	I_{FSM}	30.0							AMPS
Maximum Instantaneous Forward Voltage at 1.0A	V_F	1.1							VOLTS
Maximum DC Reverse Current TA=25°C at rated DC Blocking Voltage TA=100°C	I_R	5.0 50.0							mA
Typical Junction Capacitance (Measured at 1 MHZ and applied reverse voltage of 4.0V D.C)	C_J	15.0							pF
Typical Thermal Resistance (Thermal resistance from junction to ambint at 0.375"(9.5mm)lead length, PCB mounted	R_{qJA}	50							°C/W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-65 to +175							°C